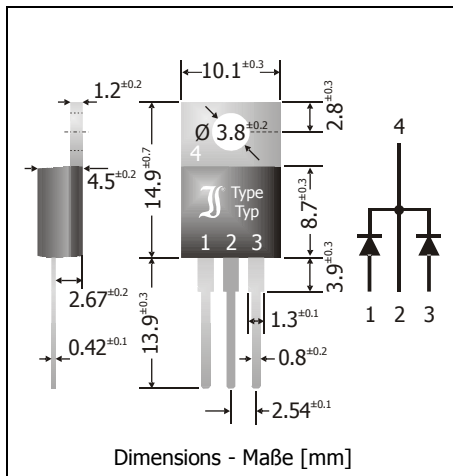


30CTQ035 ... 30CTQ045

High Temperature Schottky Rectifier – Common Cathode Hochtemperatur Schottky Gleichrichterdiode – Gemeinsame Kathode

Version 2013-05-07



Nominal current Nennstrom	2 x 15 A
Repetitive peak reverse voltage Periodische Spitzensperrspannung	35...45 V
Plastic case Kunststoffgehäuse	TO-220AB
Weight approx. Gewicht ca.	1.8 g
Plastic material has UL classification 94V-0 Gehäusematerial UL94V-0 klassifiziert	
Standard packaging in tubes Standard Lieferform in Stangen	



Maximum ratings and Characteristics

Grenz- und Kennwerte

Type Typ	Repetitive peak reverse voltage Periodische Spitzensperrspannung V_{RRM} [V] ¹⁾	Surge peak reverse voltage Stoßspitzensperrspannung V_{RSM} [V] ¹⁾	Forward voltage Durchlass-Spannung V_F [V] ¹⁾ , $T_j = 25^\circ\text{C}$	
			$I_F = 5\text{ A}$	$I_F = 15\text{ A}$
30CTQ035	35	35	< 0.52	< 0.62
30CTQ040	40	40	< 0.52	< 0.62
30CTQ045	45	45	< 0.52	< 0.62

Max. average forward current, Dauergrenzstrom	$T_C = 127^\circ\text{C}$ $T_C = 127^\circ\text{C}$	I_{FAV} I_{FAV}	15 A ²⁾ 30 A ³⁾
Repetitive peak forward current Periodischer Spitzenstrom	$f > 15\text{ Hz}$	I_{FRM}	53 A ⁴⁾
Peak forward surge current, 50 Hz half sine-wave Stoßstrom für eine 50 Hz Sinus-Halbwellen	$T_A = 25^\circ\text{C}$	I_{FSM}	265 A ¹⁾
Rating for fusing, $t < 10\text{ ms}$ Grenzlastintegral, $t < 10\text{ ms}$	$T_A = 25^\circ\text{C}$	i^2t	351 A ² s ¹⁾
Junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur		T_j T_s	-50...+175°C -50...+175°C

1 Per diode – Pro Diode

2 50% Duty Cycle, Rectangular waveform - 50% Duty Cycle, Rechteckwellenform

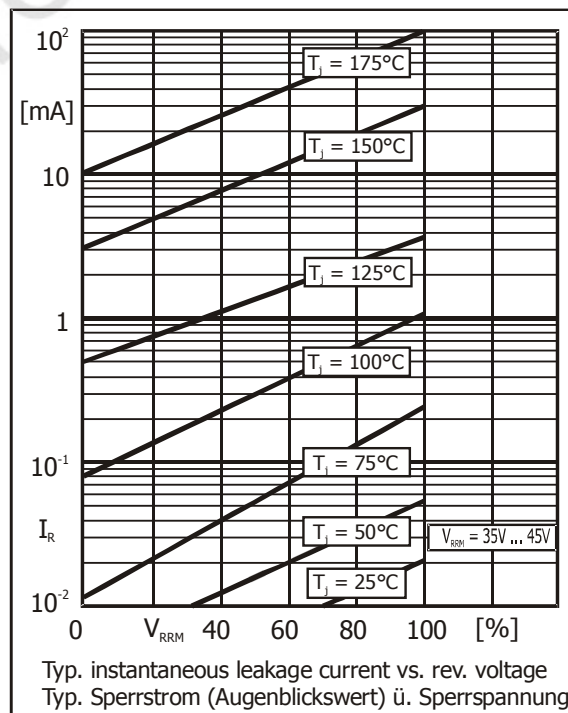
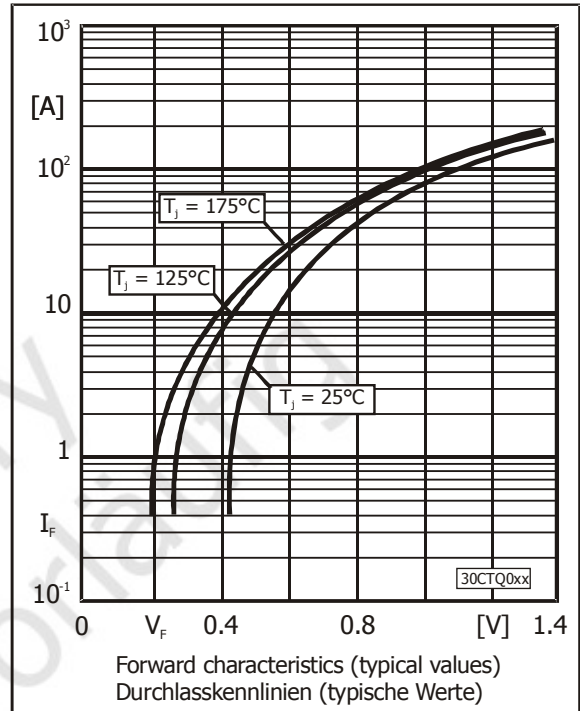
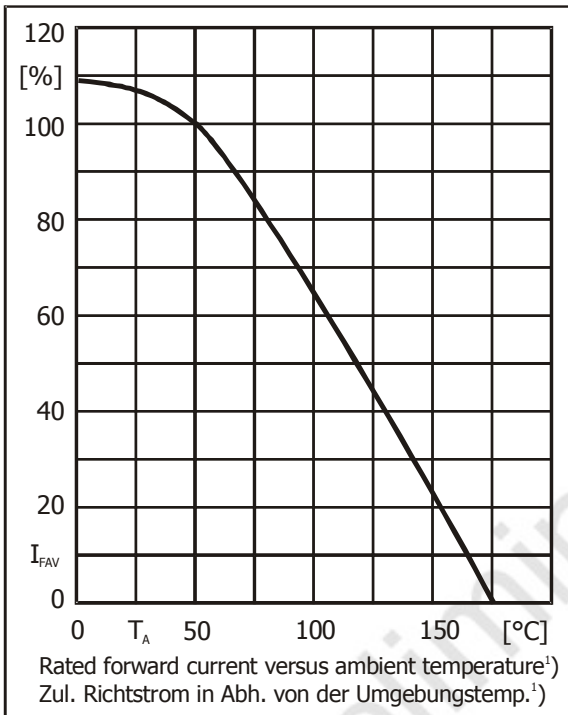
3 Per device (parallel operation) – Pro Bauteil (Parallelbetrieb)

4 Max. temperature of the case $T_C = 100^\circ\text{C}$ – Max. Temperatur des Gehäuses $T_C = 100^\circ\text{C}$

Characteristics

Kennwerte

Leakage current Sperrstrom	$T_j = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_j = 125^\circ\text{C}$ $V_R = V_{RRM}$	I_R	< 50 μA < 15 mA
Thermal resistance junction to case Wärmewiderstand Sperrschicht – Gehäuse		R_{thc}	< 3.25 $\text{K/W}^{1)}$
Maximum Junction Capacitance Maximale Sperrschichtkapazität		C_j	900 $\text{pF}^{1)}$



1 Per diode – Pro Diode